## AN1895 <br> Application note

## EVAL6562-375W Evaluation Board <br> L6562-based 375W FOT-controlled PFC Pre-regulator

## Introduction

This application note describes a 375W evaluation board based on the 26562 Transitionmode Power Factor Correction (PFC) controller (order code: EVAL6562-375W).

The board implements a 375 W , wide-range mains input, PFC pre-regulator that is suitable for a 300/350W ATX12V power supply unit (PSU).
To enable the use of a low-cost device like the L6562 at a power level that is usually prohibitive for this device, the chip operates with a Fixed-Off-Time (FOT) control system. This allows Continuous Conduction Mode operation, normally achievable with more expensive control chips and more complex control architectures.

EVAL6562-375W evaluation board


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## 1 Board description

The EVAL6562-375W evaluation board includes a Power Factor Correction (PFC) preregulator for a 300W ATX 12V power supply unit (PSU). It is able to deliver 375W continuous power on a regulated 400 V rail from a wide range of mains voltage. This rail will be the input for the cascaded isolated DC-DC converter (typically a forward converter) that will provide the output rails of the silver box. Although the ATX specification envisages air cooling, typically realized with a fan capable of an airflow in the range of 25-35 CFM, this is not allowed for in the design of this evaluation board. Enough heat sinking will be provided to allow full-load operation in still air. With an appropriate airflow and without any change in the circuit, the evaluation board can easily deliver up to 400-420W.

The L6562 controller chip is designed for Transition-Mode (TM) operation where the boost inductor works next to the boundary between Continuous (CCM) and Discontinuous Conduction Mode (DCM). However, with a slightly different usage, the chip can operate so that the boost inductor works in CCM, hence surpassing the limitations of TM operation in terms of power handling capability. The gate-drive capability of the $\mathrm{L} 6562( \pm 0.8 \mathrm{~A} \mathrm{~min}$.) is also adequate to drive the MOSFETs used at higher power levels.

This approach, which couples the simplicity and cost-effectiveness of TM operation with the high-current capability of CCM operation, is the Fixed-Off-Time (FOT) control. The control modulates the ON-time of the power switch, while its OFF-time is kept constant. More precisely, it will be used the Line-Modulated FOT (LM-FOT) where the OFF-time of the power switch is not rigorously constant but is modulated by the instantaneous mains voltage. Please refer to [2] for a detailed description of this technique.

Table 1 summarizes the electrical specification of the application and Table 3 lists transformer specifications.
The electrical schematic is shown in Figure 1 and the PCB layout in Figure 2.
Appendix $A$ lists the bill of materials.
Table 1. Electrical specifications

| Parameter | Value |
| :--- | :---: |
| Line voltage range | 90 to $265 \mathrm{~V}_{\mathrm{AC}}$ |
| Minimum line frequency ( $\mathrm{f}_{\mathrm{L}}$ ) | 47 Hz |
| Regulated output voltage | 400 V |
| Rated output power | 375 W |
| Maximum $2 \mathrm{f}_{\mathrm{L}}$ output voltage ripple | $20 \mathrm{~V} \mathrm{pk-pk}$ |
| Hold-up time | 17 ms |
| Maximum switching frequency $\left(@ \mathrm{~V}_{\mathrm{IN}}=90 \mathrm{~V}_{\mathrm{AC}}, \mathrm{P}_{\mathrm{OUT}}=375 \mathrm{~W}\right)$ | 100 kHz |
| Minimum estimated efficiency $\left(@ \mathrm{~V}_{\mathrm{IN}}=90 \mathrm{~V}_{\mathrm{AC}}, \mathrm{P}_{\mathrm{OUT}}=375 \mathrm{~W}\right)$ | $90 \%$ |
| Maximum ambient temperature | $50^{\circ} \mathrm{C}$ |

Figure 1. Electrical schematic diagram


Figure 2. PCB layout, silk + bottom layer (top view) ( $150 \times 81.5 \mathrm{~mm}$ )


## 2 Power stage design procedure

The step-by-step procedure of an LM-FOT controlled PFC pre-regulator outlined in [2] will be followed. The design will be done on the basis of a ripple factor (the ratio of the maximum current ripple amplitude to the inductor peak current at minimum line voltage) $\mathrm{Kr}=0.3$.

1. The range of $k\left(k_{\min } \div k_{\max }\right)$ associated to the line voltage range is:

$$
\mathrm{k}_{\min }=\sqrt{2} \frac{\mathrm{Vin}_{(\mathrm{RMS}) \min }}{\text { Vout }}=\sqrt{2} \frac{90}{400}=0.318, \mathrm{k}_{\max }=\sqrt{2} \frac{\mathrm{Vin}_{(\mathrm{RMS}) \max }}{\text { Vout }}=\sqrt{2} \frac{265}{400}=0.937 .
$$

2. The required $\mathrm{t}_{\mathrm{OFFm}}$ in is derived from the specification on the maximum switching frequency (on the top of the line voltage sinusoid) $f_{\text {swmax }}$ at minimum line voltage:

$$
t_{\text {OFF } \min }=\frac{k_{\min }}{f_{s w \max }}=\frac{0.318}{100 \cdot 10^{3}}=3.18 \mu \mathrm{~s}
$$

3. The maximum expected input power $\mathrm{Pin}_{0}=\mathrm{Pout}_{0} / \eta$ and the maximum line peak current, Ipk $_{\text {max }}$ are:

$$
\operatorname{Pin}_{0}=\frac{375}{0.9}=417 \mathrm{~W} ; \mathrm{Ipk}_{\max }=\frac{2 \operatorname{Pin}_{0}}{\mathrm{k}_{\min } \operatorname{Vout}}=\frac{2.417}{0.318 \cdot 400}=6.56 \mathrm{~A}
$$

4. The ripple amplitude on the top of the sinusoid at minimum line voltage, assuming it is $75 \%$ of the maximum specified, will be:

$$
\Delta \mathrm{L}_{\mathrm{Lpk}}=\frac{6 \mathrm{Kr}}{8-3 \mathrm{Kr}} \mathrm{lpk}_{\max }=\frac{6 \cdot 0.3}{8-3 \cdot 0.3} \cdot 6.56=1.66 \mathrm{~A}
$$

5. The required inductance $L$ of the boost inductor is:

$$
\mathrm{L}=\left(1-\mathrm{k}_{\min }\right) \frac{\mathrm{Vout}^{\Delta \mathrm{I}_{\text {Lpk }}}}{\mathrm{t}_{\text {OFF min }}}=(1-0.318) \cdot \frac{400}{1.66} \cdot 3.18 \cdot 10^{-6}=523 \mu \mathrm{H}
$$

This value will be rounded up to $550 \mu \mathrm{H}$; the resulting value of Kr will be slightly smaller than 0.3 , but we will go on using the target value, this will give some additional margin.
6. The maximum inductor peak current, $I_{\text {Lpkmax }}$, is calculated:

$$
\mathrm{I}_{\text {Lpkmax }}=\frac{8}{8-3 \mathrm{Kr}} \mathrm{lpk}_{\max }=\frac{8}{8-3 \cdot 0.3} \cdot 6.56=7.39 \mathrm{~A}
$$

7. The maximum sense resistor $R_{\text {sensemax }}$ is:

$$
R_{\text {sense } \max }=\frac{1.6}{I_{\text {Lpkmax }}}=\frac{1.6}{7.39}=0.216 \Omega
$$

( 1.6 V is the minimum value of the pulse-by-pulse current limiting threshold on the current sense pin of the L6562). It will be realized with four $0.68 \Omega, 1 \mathrm{~W}$-rated paralleled resistors, for a total resistance of $0.17 \Omega$. This provides some extra power capability. The inductor peak current that the inductor must be able to carry without saturating will be:

$$
I_{\text {Lpksat }}=\frac{1.8}{0.17}=10.6 \mathrm{~A}
$$

8. From the formulae in [2], table 4, the MOSFET RMS current is:

$$
\mathrm{I}_{\mathrm{Q}(\mathrm{rms})}=\frac{\mathrm{Pin}_{0}}{\mathrm{k}_{\min } \text { Vout }} \sqrt{2-\frac{16 \mathrm{k}_{\min }}{3 \cdot \pi}}=\frac{417}{0.318 \cdot 400} \sqrt{2-\frac{16 \cdot 0.318}{3 \cdot \pi}}=3.96 \mathrm{~A}
$$

The diode RMS current is:

$$
\mathrm{I}_{\mathrm{Q}(\mathrm{rms})}=\frac{\mathrm{Pin}_{0}}{\mathrm{k}_{\min } \mathrm{Vout}} \sqrt{\frac{16 \mathrm{k}_{\min }}{3 \cdot \pi}}=\frac{417}{0.318 \cdot 400} \sqrt{\frac{16 \cdot 0.318}{3 \cdot \pi}}=2.41 \mathrm{~A}
$$

The dissipation on the sense resistor will be $0.17 \cdot 3.96^{2}=2.7 \mathrm{~W}$, which justifies the use of four resistors; the selected MOSFET is the STP12NM50, a 0.3 $/ 2 / 500 \mathrm{~V}$ MDmesh ${ }^{\text {TM }}$ type from STMicroelectronics, housed in a TO220 package; two of them will be paralleled to handle the rated power; the selected diode is an STTH806DTI, an 8A/600V Tandem diode, again from STMicroelectronics, housed in a TO220 package. All of them must be dissipated to keep their temperature within safe limits.
As for the inductor, the core size will be determined by saturation since the ripple is relatively low. Assuming a peak flux density $\operatorname{Bmax}=0.3 T$, the minimum required AreaProduct is:

$$
A P_{\min } \approx 186\left(\frac{1-\mathrm{k}_{\min } \mathrm{Kr}}{\mathrm{k}_{\min } \mathrm{Kr}} \frac{\mathrm{Pin}_{0} \mathrm{t}_{\mathrm{OFF}}}{\mathrm{~B}_{\max }}\right)^{1.31}=186\left(\frac{1-0.318 \cdot 0.3}{0.318 \cdot 0.3} \frac{417 \cdot 3.18 \cdot 10^{-6}}{0.3}\right)^{1.31}=2.92\left[\mathrm{~cm}^{4}\right]
$$

An E42 core ( $\mathrm{AP}=3.15 \mathrm{~cm}^{4}$ ) has been chosen. See table 3 for the complete inductor spec.
The output capacitor is determined by the hold-up time requirement. Assuming a minimum voltage of 300 V after the line drop, a minimum of $180 \mu \mathrm{~F}$ is needed and a $220 \mu \mathrm{~F} / 450 \mathrm{~V}$ capacitor will be used.
9. The peak multiplier bias voltage $\mathrm{V}_{\mathrm{MULT}} @ 90 \mathrm{~V}$ mains must meet the condition:

$$
\frac{\mathrm{I}_{\text {Lpkmax }} \mathrm{R}_{\text {sense }}}{1.65} \leq \mathrm{V}_{\text {MULTpk }} \leq 3 \frac{\mathrm{~V}_{\text {in(RMS }) \min }}{\mathrm{V}_{\text {in(RMS }) \max }}
$$

where 1.65 is the minimum slope of the multiplier characteristic associated to the error amplifier saturated high (see Figure 9 in [1]). With the selected value for Rsense (0.17 $\Omega$ ):

$$
\frac{7.39 \cdot 0.17}{1.65}=0.761 \leq \mathrm{V}_{\mathrm{MULTpk}} \leq 3 \cdot \frac{90}{265}=1.02
$$

Choosing the ratio of the resistor divider that biases the multiplier input (pin 3, MULT) $\mathrm{K}_{\mathrm{P}}=8 \cdot 10^{-3}$ lets the peak voltage on the multiplier pin will go from 1 V to 3 V , thus meeting the above condition.
The high-side resistor of the output divider that sets the output voltage is chosen on the basis of the maximum allowed overvoltage on the output. Considering 40V overvoltage, the high-side resistor must be $1 \mathrm{M} \Omega$ (see [3] for details, in this respect the L6561 and the L6562 are exactly equal). The low-side resistor will then be $1 \mathrm{M} \Omega \cdot(400 / 2.5-1)$ $=6.29 \mathrm{k} \Omega$; the $6.34 \mathrm{k} \Omega$ standard value will be used.

Based on the model given in [2], a compensation network made with an RC series ( $\mathrm{R}=6.8 \mathrm{k} \Omega, \mathrm{C}=1 \mu \mathrm{~F}$ ) guarantees a minimum of $25^{\circ}$ phase margin (with 9 Hz bandwidth) at minimum line and a bandwidth not exceeding 20 Hz (with $50^{\circ}$ phase margin) at maximum line.

## 3 Setting up FOT control with the L6562

FOT control is implemented with the L6562 using the circuit shown in Figure 3, which shows some significant waveforms as well. Before starting the design, the desired value of $t_{\text {OFF }}$ at the maximum line voltage must be specified. Application note AN1792 shows that to reduce high-voltage distortion, $\mathrm{t}_{\mathrm{OFF}}$ must be greater than $7 \mu \mathrm{~s}$, hence we choose $\mathrm{t}_{\mathrm{OFF}}=8 \mu \mathrm{~s}$.

Figure 3. Circuit implementing FOT control with the L6562 and relevant timing waveforms.


Following the design procedure given in AN1792, with the aid of the diagram of Figure 4:

1. The ratio of the maximum $t_{\mathrm{OFF}}$ value to the minimum $\mathrm{t}_{\mathrm{OFF}}$ value is:

$$
\rho=\frac{8 \cdot 10^{-6}}{3.18 \cdot 10^{-6}}=2.52
$$

2. Consider the value of $\mathrm{V}_{\text {MULTpk }}$ at minimum line voltage $\left(\mathrm{V}_{\mathrm{MULTpk}}=1 \mathrm{~V}\right)$, in Figure 4 draw a horizontal line located at $\rho=2.52$ (on the left vertical axis) as long as it intercepts the $\rho$ curve relevant to the value $\mathrm{V}_{\text {MULTpk }}=1 \mathrm{~V}$ in P 1 . The abscissa of P 1 gives the value $\mathrm{K} 1=0.891$.
3. From P1 draw a vertical line as long as it intercepts the K 2 curve relevant to $\mathrm{V}_{\mathrm{MULTpk}}=1$ in P2. The ordinate of P2 (on the right vertical axis) gives the value $\mathrm{K} 2=4.17$.
4. The required time constant is:

$$
\tau=\frac{\mathrm{t}_{\mathrm{OFFmin}}}{\mathrm{~K} 2}=\frac{3.18 \cdot 10^{-6}}{4.17}=0.76 \cdot 10^{-6} \mathrm{~s}
$$

5. A capacitor $\mathrm{C}=560 \mathrm{pF}$ is selected, then the associated resistance value will be:

$$
\mathrm{R}^{\prime}=\frac{\tau}{\mathrm{C}}=\frac{0.76 \cdot 10^{-6}}{560 \cdot 10^{-12}}=1357 \Omega
$$

6. R1 and R2 will be respectively:

$$
\mathrm{R} 1=\frac{\mathrm{R}^{\prime}}{1-\mathrm{K} 1}=\frac{1357}{1-0.891}=12450 \Omega \quad \mathrm{R} 2=\frac{\mathrm{R}^{\prime}}{\mathrm{K} 1}=\frac{1357}{0.891}=1523 \Omega
$$

the standard values $R 1=12 \mathrm{k} \Omega$ and $R 2=1.5 \mathrm{k} \Omega$ will be chosen.
7. Assuming that the $\mathrm{V}_{\mathrm{CC}}$ voltage never falls below $14-15 \mathrm{~V}$, the limiting resistor Rs can be selected according to:

$$
\mathrm{Rs}>\frac{\mathrm{V}_{\mathrm{GDx}}-\mathrm{V}_{\mathrm{ZCDclamp}}-\mathrm{V}_{\mathrm{F}}}{\mathrm{I}_{\mathrm{ZCDx}}+\frac{\mathrm{V}_{\mathrm{ZCDClamp}} \mathrm{R} 2+\left(\mathrm{V}_{\mathrm{ZCDclamp}}-\mathrm{V}_{\mathrm{MULTpkmax}}-\mathrm{V}_{\mathrm{BE}}\right) \mathrm{R} 1}{\mathrm{R} 1 \mathrm{R} 2}}
$$

where $\mathrm{V}_{\mathrm{GDx}}=15 \mathrm{~V}$ is the maximum clamp value of the gate drive voltage, $\mathrm{V}_{\mathrm{ZCD} \text { clamp }} \approx$ 5.7 V is the clamp value of the ZCD pin voltage, $\mathrm{V}_{\mathrm{F}} \approx 0.5 \mathrm{~V}$ the forward drop on the diode, $\mathrm{I}_{\mathrm{ZCDx}}=10 \mathrm{~mA}$ the maximum ZCD clamp current D and $\mathrm{V}_{\mathrm{BE}} \approx 0.55 \mathrm{~V}$ the emitter-to-base forward drop of T. Substituting:

$$
R s>\frac{15-5.7-0.5}{10 \cdot 10^{-3}+\frac{5.7 \cdot 1500+(5.7-3-0.55) \cdot 12000}{1500 \cdot 12000}}=739 \Omega
$$

in this case a $1.5 \mathrm{k} \Omega$ resistor will be chosen
8. Cs will be selected according to the relationship:

$$
\mathrm{Cs}<\mathrm{C} \frac{\mathrm{~V}_{\mathrm{ZCDclamp}}}{\mathrm{~V}_{\mathrm{GDx}}-\mathrm{V}_{\mathrm{ZCDclamp}}-\mathrm{V}_{\mathrm{F}}}=560 \cdot 10^{-12} \frac{5.7}{15-5.7-0.5}=363 \mathrm{pF}
$$

a standard value $\mathrm{Cs}=330 \mathrm{pF}$ will be used.
Figure 4. Diagrams for the design of the circuit of Figure 3 (valid for wide-range mains operation).


## 4 Getting started with the evaluation board

The $A C$ voltage, generated by an $A C$ source ranging from 90 to $265 \mathrm{~V}_{\mathrm{AC}}$, will be applied to the input connector, located close to the bottom left-hand corner.
The $400 \mathrm{~V}_{\mathrm{DC}}$ output is located close to the bottom right-hand corner and will be connected to the load. If an electronic load is going to be used pay attention to the right polarity: the (+) output terminal is that located closer to the corner.

Warning: Like in any offline circuit, extreme caution must be used when working with the application board because it contains dangerous and lethal potentials.

The application must be tested with an isolation transformer connected between the AC mains and the input of the board to avoid any risk of electrical shock.

### 4.1 Testbench results and significant waveforms

The following diagrams summarize the results of certain testbench evaluations. A number of waveforms under different load and line conditions are shown for user's reference.

Figure 5. Evaluation data


Figure 6. Compliance with JEIDA-MITI \& EN61000-3-2 standards


Figure 7. Harmonic emissions at light load (70W)


Figure 8. Line current waveforms $@$ POUT $=375 \mathrm{~W}$


Figure 9. Line current waveforms @ P


Figure 10. Line current waveforms @ $\mathrm{P}_{\text {OUT }}=70 \mathrm{~W}$


Ch1: Input voltage (after the bridge rectifier)
Ch2: Line current $\left(@ V_{\text {IN }}=115 V_{\text {AC }}, P_{\text {OUT }}=70 \mathrm{~W}\right)$


Ch1: Input voltage (after the bridge rectifier)
Ch2: Line current $\left(@ V_{I N}=230 V_{\text {AC }}, P_{\text {out }}=70 \mathrm{~W}\right)$

Note: 1 Note that input LC filter is provided only to clean the line current waveform enough to prevent the measurement system from being misled by an excessive noise level. The filter is not designed nor tested for EMI compliance.
2 The board, as is, is able to handle properly an output load as low as 15 W . With lower load levels, the system will not start up correctly at low line because the OVP generated at startup lasts so long that the $V_{C C}$ voltage drops below the UVLO of the L6562 (e.g. with 4 W load the system would stop for $600 \mathrm{~ms} @ V_{I N}=90 V_{A C}$ ). Load transients from the maximum load to levels below 15 W may cause the $V_{C C}$ to be lost as well. If supplying the $L 6562$ with an external source, the minimum load that can be handled properly drops to virtually zero.

## 5 References

[1] "L6562 Power Factor Corrector" Datasheet.
[2] "Design of Fixed-Off-Time-Controlled PFC Pre-regulators with the L6562", AN1792.
[3] "L6561, Enhanced Transition-Mode Power Factor Corrector", AN966.

## Appendix A Bill of materials

Table 2. Bill of material for EVAL6562-375W evaluation board

| Symbol | Value | Note |
| :---: | :---: | :---: |
| R1A and R1B | $120 \mathrm{k} \Omega$ |  |
| R2A and R2B | $620 \mathrm{k} \Omega$ |  |
| R3 | $10 \mathrm{k} \Omega$ |  |
| R4 | $47 \Omega$ |  |
| R5 | $6.8 \mathrm{k} \Omega$ |  |
| R6 and R13 | $6.8 \Omega$ |  |
| R7A, R7B, R7C and R7D | $0.68 \Omega$ | Metal film, 1W |
| R8 and R12 | $1.5 \mathrm{k} \Omega$ |  |
| R9 | $12 \mathrm{k} \Omega$ |  |
| R10A and R10B | $499 \mathrm{k} \Omega$ |  |
| R11 | $6.34 \mathrm{k} \Omega$ |  |
| R14 | $330 \Omega$ |  |
| CX1 and CX2 | 330 nF | EPCOS B81131 or equivalent |
| C1 | $1 \mu \mathrm{~F}$ | 400V, EPCOS B32653 or equivalent |
| C2 and C4 | 10 nF |  |
| C3 | $47 \mu \mathrm{~F}$ | 25 V electrolytic |
| C5 | $1 \mu \mathrm{~F}$ |  |
| C6 and C10 | 330 pF |  |
| C7 | 560 pF |  |
| C8 | 470 nF | 630V, EPCOS B32653 or equivalent |
| C9 | $220 \mu \mathrm{~F}$ | 450 V , Electrolytic Nichicon LS or equivalent |
| L1 | TOR73 | $3.9 \mathrm{mH} / 6 \mathrm{~A}$, supplied by ITACOIL s.r.I. |
| T1 | E4218 | Boost inductor. See spec on table 3. Supplied by ITACOIL s.r.I. |
| BRIDGE | KBU8M | 8A / 1000V, GI or equivalent |
| D1, D2, D3 and D4 | 1N4148 | $0.3 \mathrm{~A} / 75 \mathrm{~V}$, glass case, Vishay or equivalent |
| D5 | 1N5406 | 3A / 600V, D0201, ON Semiconductor or equivalent |
| D6 | STTH806DTI | 8A / 600V, Tandem Hyperfast, TO220, ST |
| DZ1 | 1N5248B | 18V / 500mW Zener, ON Semiconductor or equivalent |
| U1 | L6562 | TM PFC controller, DIP8, ST |
| M1 and M2 | STP12NM50FP | $0.3 \Omega$ / 500V, MDmesh ${ }^{\text {TM }}$, TO220FP, ST |
| TR1 | BC557 | PNP, 0.1A / 45V, TO92, On Semiconductor or equivalent |
| NTC1 | BS237 | NTC $2.5 \Omega$, EPCOS or equivalent |
| F1 | --- | 8A, 250V |
| PCB | --- | FR-4, Cu single layer $35 \mu \mathrm{~m}, 150 \times 81.5 \mathrm{~mm}$ |
| Heat sink | OS512 | $2.12{ }^{\circ} \mathrm{C} / \mathrm{W}$, Extrusion Profile, Aavid Thermalloy |

Note: If not otherwise specified, all resistors are $1 \%, 1 / 4 \mathrm{~W}$, all capacitors are ceramic or plastic film.
The Bridge, M1, M2 and D6 all share the same heat sink.

Table 3. EVAL6562-375W: boost inductor specification (part\# E4218, made by ITACOIL s.r.I.)

| Core | E42/21/7, N67 Material or equivalent |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :--- |
| Bobbin | Horizontal mounting, 10 pins |  |  |  |  |
| Air gap | $\approx 1.9 \mathrm{~mm}$ for an inductance 1-10 of $550 \mu \mathrm{H}$ |  |  |  |  |
| Windings <br>  <br> Build | Pin <br> Start/End | Winding | Wire | Turns | Notes |
|  | $1 / 10$ | Main | $20 x$ AWG32 | 58 (N1) | Pins 1 \& 2, pins $10 \& 9$ are shorted on the PCB |
|  | $6 / 5$ | Aux | AWG32 | 6 (N2) | Evenly spaced |

## Revision history

Table 4. Document revision history

| Date | Revision | Changes |
| :---: | :---: | :--- |
| 20-May-2004 | 2 | Initial release. |
| 28-Aug-2006 | 3 | Corrected Equation 1. on page 5. Minor editing changes. |

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